

METHOD FOR CONTROLLING AND MONITORING A CHEMICAL
MECHANICAL POLISHING PROCESS

ABSTRACT

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The present invention relates a method of controlling and monitoring the thickness variation of the film structure of a semiconductor wafer by monitoring the thickness variation of the film structure of a testing region. The method is characterized by etching the film structure of the testing region with
10 a pattern density substantially compatible with that of the device region in order to precisely simulate the thickness variation of the film structure of a device region in a chemical mechanical polishing process.